

P-Channel 100 V (D-S) MOSFET



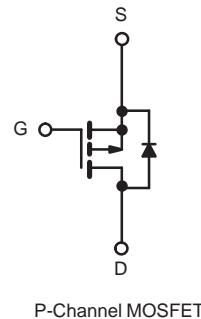
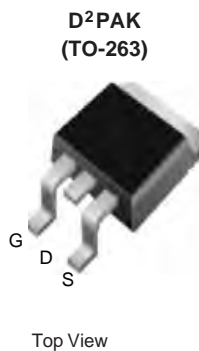
PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
- 100	0.010 at V _{GS} = - 10 V	-110	165
	0.014 at V _{GS} = - 4.5 V	-100	

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested

APPLICATIONS

- Power Switch
- DC/DC Converters
- Portable equipment and battery powered systems



ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 100	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	- 110
		T _C = 75 °C	-92
Pulsed Drain Current	I _{DM}	- 300	A
Avalanche Current	I _{AS}	- 72	
Single Avalanche Energy ^a	E _{AS}	275	mJ
Maximum Power Dissipation ^a	P _D	T _C = 25 °C	368 ^b
		T _A = 25 °C ^c	8.2
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	42	°C/W
Junction-to-Case (Drain)	R _{thJC}	1.0	

Notes:

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When Mounted on 1" square PCB (FR-4 material).

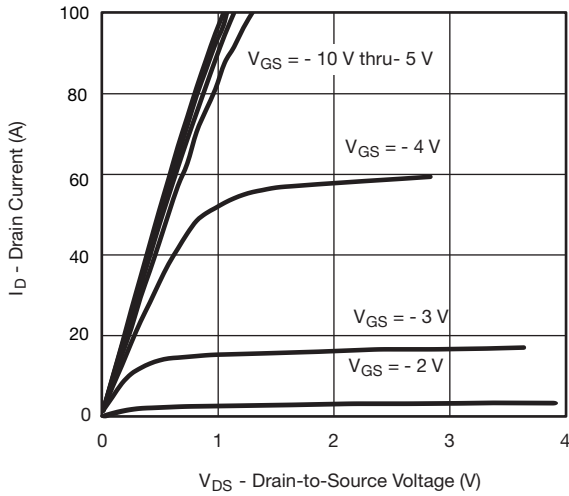
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{DS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1		- 3.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			- 50	
		$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$			- 250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -10\text{ V}, V_{GS} = -10\text{ V}$	- 110			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -30\text{ A}$		0.010	0.014	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -20\text{ A}$		0.014	0.020	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -20\text{ A}$		57		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -50\text{ V}, f = 1\text{ MHz}$		9450		μF
Output Capacitance	C_{oss}			1205		
Reverse Transfer Capacitance	C_{rss}			350		
Total Gate Charge ^c	Q_g	$V_{DS} = -50\text{ V}, V_{GS} = -10\text{ V}, I_D = -30\text{ A}$		165		nC
		$V_{DS} = -50\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -20\text{ A}$		130		
Gate-Source Charge ^c	Q_{gs}			43		
Gate-Drain Charge ^c	Q_{gd}			48		
Gate Resistance	R_g	$f = 1\text{ MHz}$	1.2	5.5	13.5	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = -50\text{ V}, R_L = 17.2\text{ }\Omega$ $I_D \cong -30\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		28		ns
Rise Time ^c	t_r			42		
Turn-Off Delay Time ^c	$t_{d(off)}$			106		
Fall Time ^c	t_f			33.5		
Drain-Source Body Diode Ratings and Characteristics $T_C = 25\text{ }^\circ\text{C}$ ^b						
Continuous Current	I_S				- 100	A
Pulsed Current	I_{SM}				- 300	
Forward Voltage ^a	V_{SD}	$I_F = -30\text{ A}, V_{GS} = 0\text{ V}$		- 0.7	- 1.5	V
Reverse Recovery Time	t_{rr}	$I_F = -30\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		90		ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			- 7	- 12	A
Reverse Recovery Charge	Q_{rr}			390	650	nC

Notes:

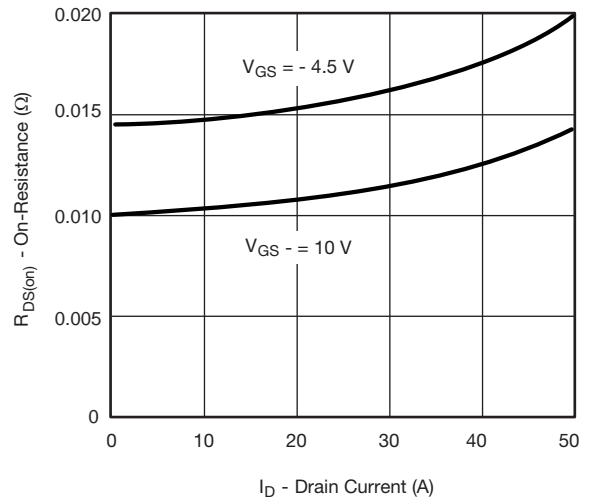
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

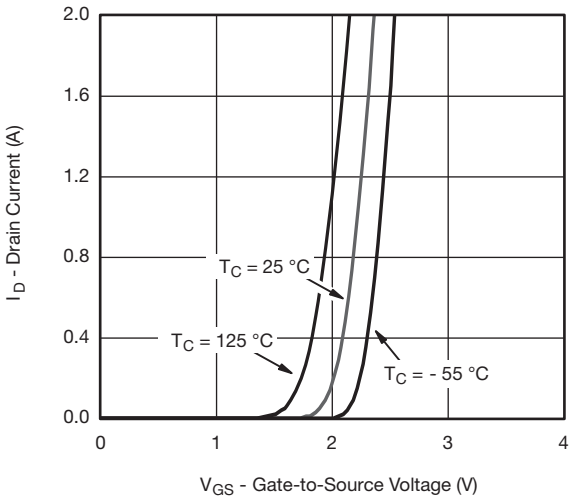
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



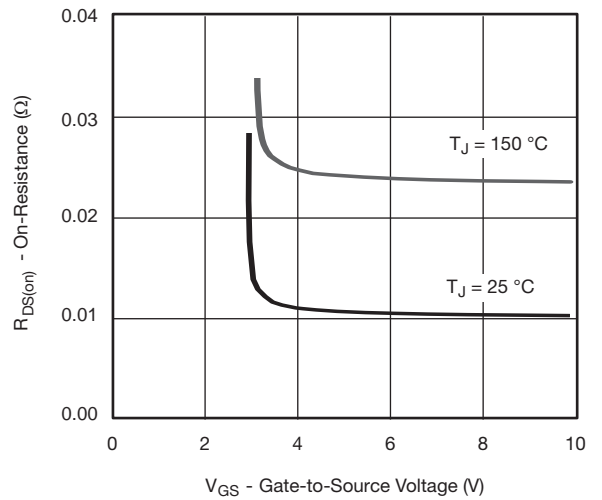
Output Characteristics



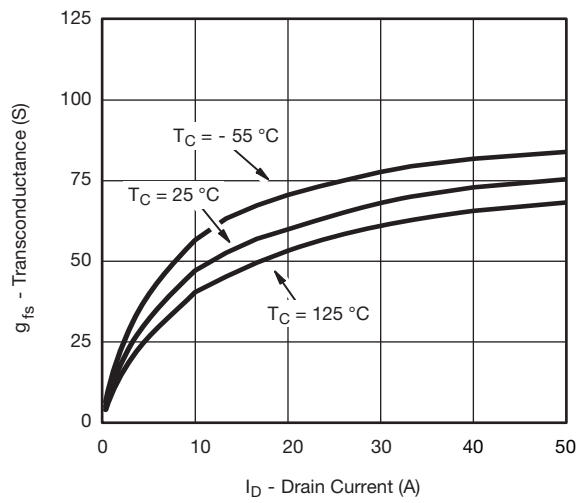
On-Resistance vs. Drain Current



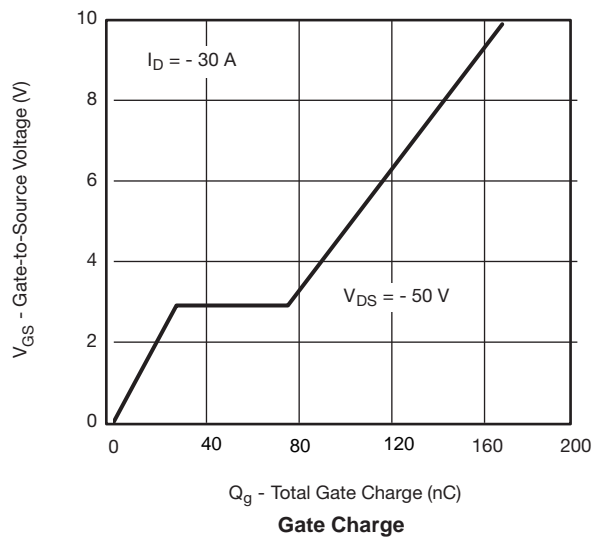
Transfer Characteristics



On-Resistance vs. Gate-to-Source Voltage

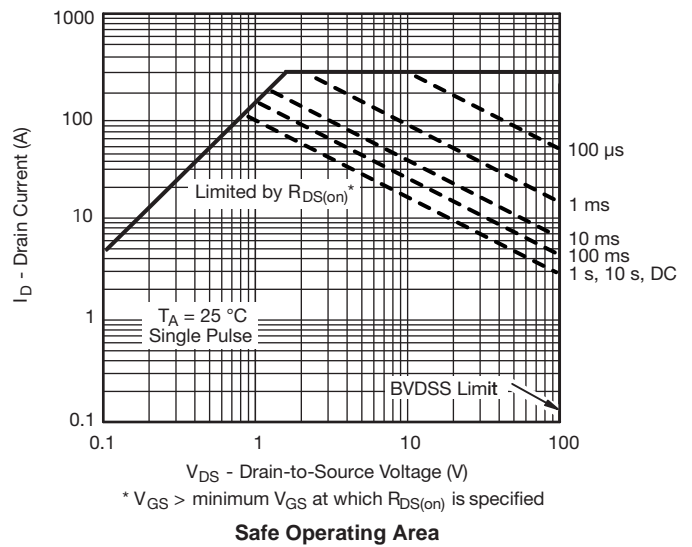
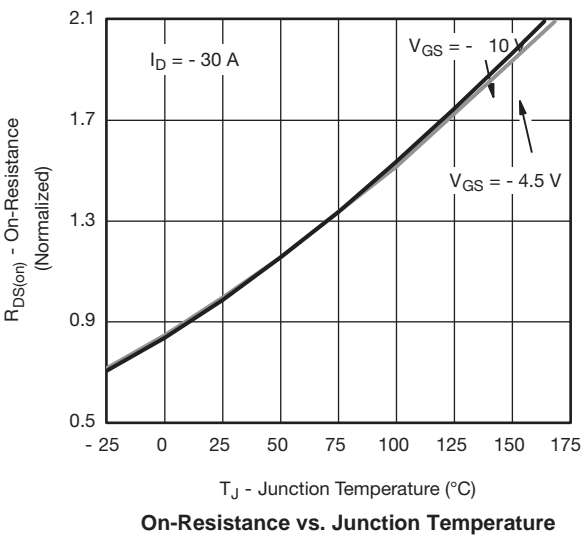
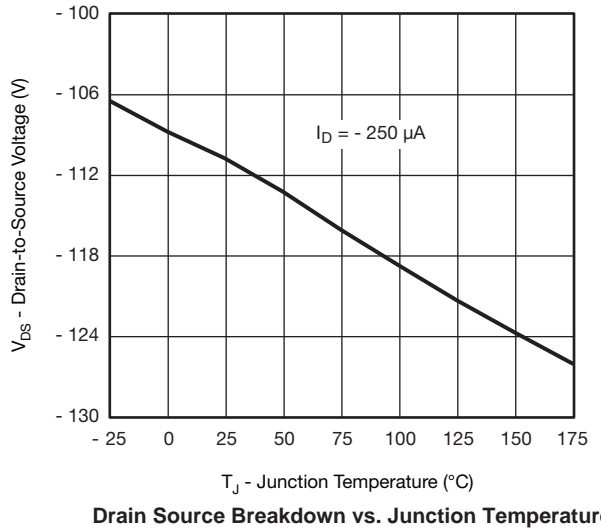
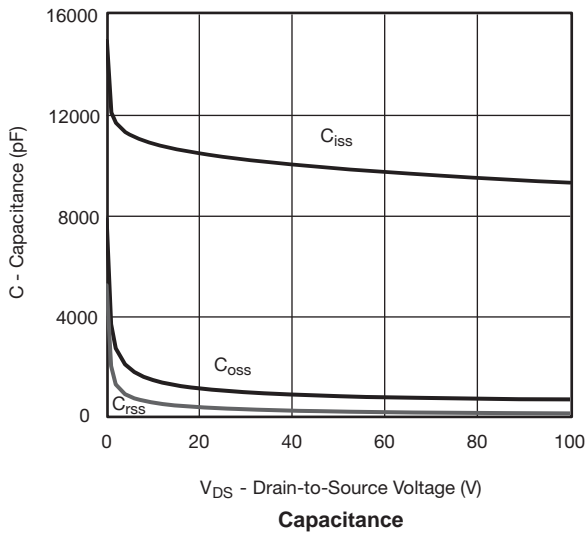
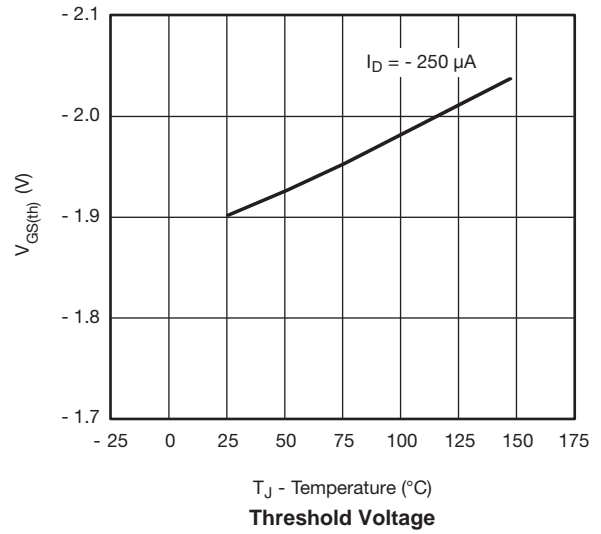
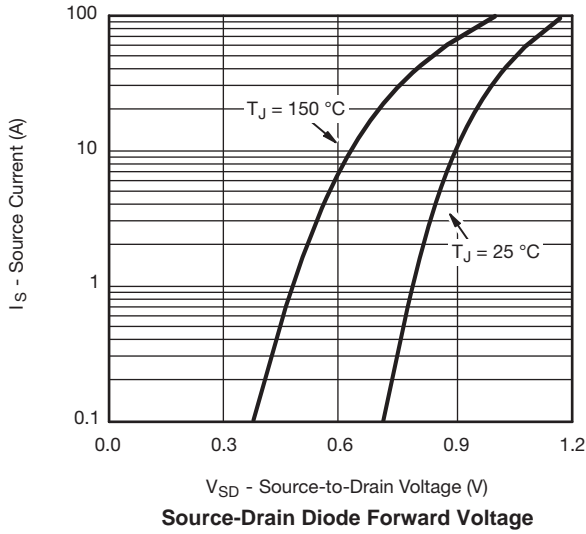


Transconductance

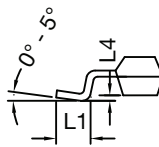
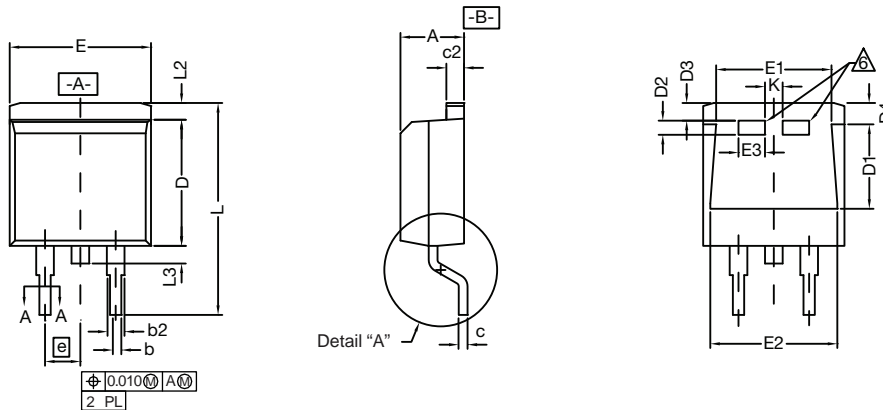


Gate Charge

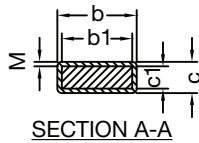
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



TO-263 (D²PAK): 3-LEAD



DETAIL A (ROTATED 90°)



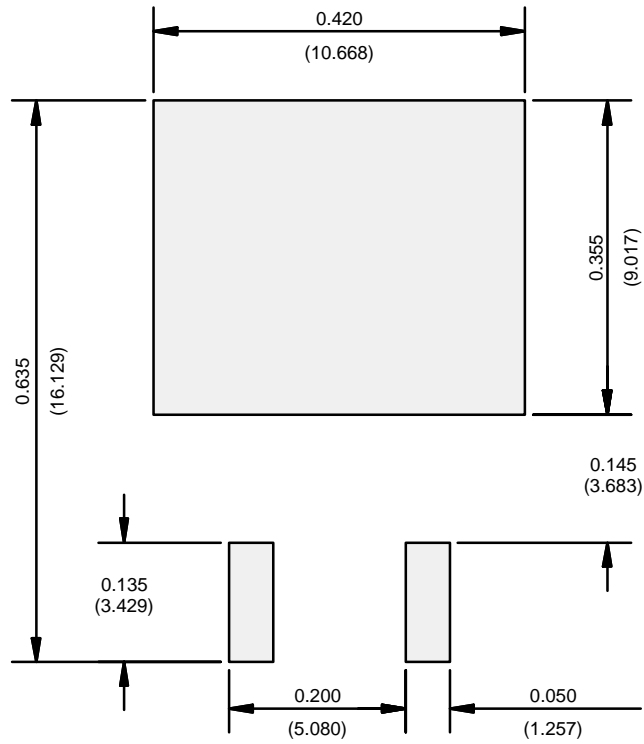
SECTION A-A

DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
E3	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

Notes

1. Plane B includes maximum features of heat sink tab and plastic.
2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
3. Pin-to-pin coplanarity max. 4 mils.
4. *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
5. Use inches as the primary measurement.
6. This feature is for thick lead.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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